

# BRCS035N03ZC

Rev.A Dec.-2023

DATA SHEET

PDFN5x6 / N-Channel MOSFET in a PDFN5x6 Plastic Package.

N-Channel MOSFET in a PDFN5x6 Plastic Package.

$V_{DS}(V)=30\text{ V}$       $I_D=95\text{ A}$

$R_{DS(ON)}@10\text{ V}$  3.6mΩ (Typ.3.5mR)

$R_{DS(ON)}@4.5\text{ V}$  6.5mΩ (Typ.5.0mR)

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Battery Management, High Frequency Point-of-

### Table 1: Absolute Maximum Ratings (T<sub>a</sub>=25 °C)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V <sub>DS</sub>	30	V
Continuous Drain Current	I <sub>D</sub>	95	A
Pulsed Drain Current	I <sub>DM</sub>	175	A
Gate-Source Voltage	V <sub>GS</sub>	±20	V
Power Dissipation	P <sub>D</sub> (T <sub>c</sub> =25 °C)	55	W
Avalanche energy(L=0.5mH)	E <sub>AS</sub>	281	mJ
Avalanche Current(L=0.5mH)	I <sub>AS</sub>	26.5	A
Junction and Storage Temperature Range	T <sub>j</sub> , T <sub>stg</sub>	-55 to 150	-
Maximum Junction-to-Ambient	t ≤ 10s	25	/ W
	Steady-State	55	
Maximum Junction-to-Case	Steady-State	2.3	

### Table 2: Electrical Characteristics (T<sub>a</sub>=25 °C)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	I <sub>D</sub> =250µA, V <sub>GS</sub> =0V	30	33		V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V			1.0	µA
Gate-Body leakage current	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> = ±20V			±100	nA
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250µA	1	1.7	3.0	V
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =20A		3.5	3.6	m S
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =10A		5.0	6.5	
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =1A, V <sub>GS</sub> =0V			1.4	V
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V f=1.0MHz		2200		pF
Output Capacitance	C <sub>oss</sub>			145		
Reverse Transfer Capacitance	C <sub>rss</sub>			210		
Gate resistance	R <sub>g</sub>	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V f=1MHz		2.0		

Electrical Characteristics(Ta=25 °C ; )

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Total Gate Charge	$Q_{g(10V)}$	$V_{GS}=10V$ $V_{DS}=15V$ $I_D=20A$		32		nC
Total Gate Charge	$Q_{g(4.5V)}$			15		
Gate Source Charge	$Q_{gs}$			5.2		
Gate Drain Charge	$Q_{gd}$			6.5		
Turn-On Delay Time	$t_{d(on)}$	$V_{GS}=10V$ $V_{DS}=15V$ $R_L=0.75 \Omega$ $R_{GEN}=3 \Omega$		8.5		ns
Turn-On Rise Time	$t_r$			4.2		
Turn-Off Delay Time	$t_{d(off)}$			30		
Turn-Off Fall Time	$t_f$			5.7		

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Company Code

Product Type Code

Lot No. Code, code change with Lot No

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<sup>a</sup> ϕ y

1o• Ä ½ “ † 150 ½180 - k ž • 60 ½90sec;

2o• Q › “ † 245 r5 - k ž • 4 Ò 5 r0.5sec;

3o•D N ò i Ò 0 , † 2 ½10 - /sec.

Note:

1.Preheating:150~180 - , Time:60~90sec.

2.Peak Temp.:245 r5 - , Duration:5 r0.5sec.

3. Cooling Speed: 2~10 - /sec.

ÂD /Cã p ~ » ] / Resistance to Soldering Heat Test Conditions

“ † y 260 r5 -

ž • y 10 r1 sec.

Temp.:260±5

Time:10±1 sec

G P á / Packaging SPEC.

2 & x / REEL

Package Type /x¥”	Units ;>û iH	Dimension ;>û p . (unit Ånm <sup>3</sup> )
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